

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-60V	350mΩ @ V _{GS} = -10V	-1.5A
	550mΩ @ V _{GS} = -4.5V	-1.2A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

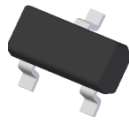
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

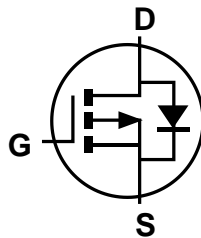
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Mechanical Data

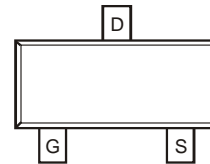
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Top View



Internal Schematic



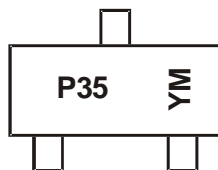
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP6350S-7	SOT23	3,000/Tape & Reel
DMP6350S-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



P35 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: D = 2016)
 M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	C	D	E	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 6), $V_{GS} = -10\text{V}$	I_D	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	A
			-1.5 -1.2
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	-6	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	0.72	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	176	$^\circ\text{C/W}$
Power Dissipation (Note 6)	P_D	1.17	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 6)	$R_{\theta JA}$	108	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	34	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	-	-	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	-	-	-1.0	μA	$V_{DS} = -60\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	-1.8	-3.0	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	257	350	m Ω	$V_{GS} = -10\text{V}, I_D = -0.9\text{A}$
		-	343	550		$V_{GS} = -4.5\text{V}, I_D = -0.8\text{A}$
Diode Forward Voltage	V_{SD}	-	-0.8	-1.2	V	$V_{GS} = 0\text{V}, I_S = -1\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	206	-	pF	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	15	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	11	-	pF	
Gate Resistance	R_g	-	17	-	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = -4.5\text{V}$)	Q_g	-	2.0	-	nC	$V_{DS} = -30\text{V}, I_D = -0.9\text{A}$
Total Gate Charge ($V_{GS} = -10\text{V}$)	Q_g	-	4.1	-	nC	
Gate-Source Charge	Q_{gs}	-	0.5	-	nC	
Gate-Drain Charge	Q_{gd}	-	0.8	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	3.6	-	ns	$V_{DD} = -30\text{V}, V_{GS} = -10\text{V}, I_D = -1.0\text{A}, R_g = 6\Omega$
Turn-On Rise Time	t_R	-	3.8	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	12.3	-	ns	
Turn-Off Fall Time	t_F	-	7.3	-	ns	
Body Diode Reverse Recovery Time	t_{RR}	-	8.2	-	ns	$I_S = -1.0\text{A}, di/dt = -100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	-	2.7	-	nC	$I_S = -1.0\text{A}, di/dt = -100\text{A}/\mu\text{s}$

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

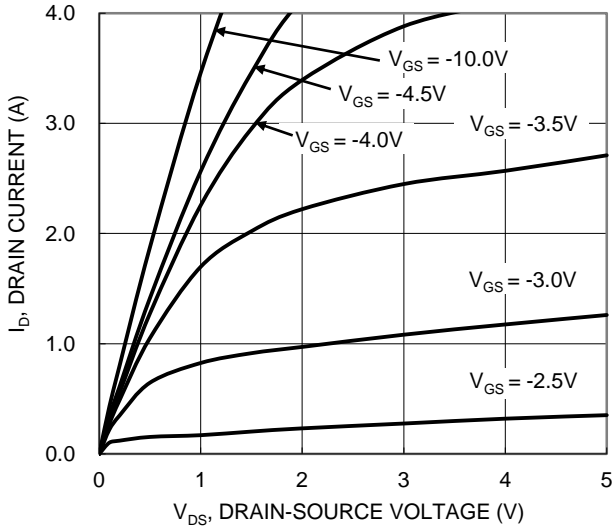


Figure 1. Typical Output Characteristic

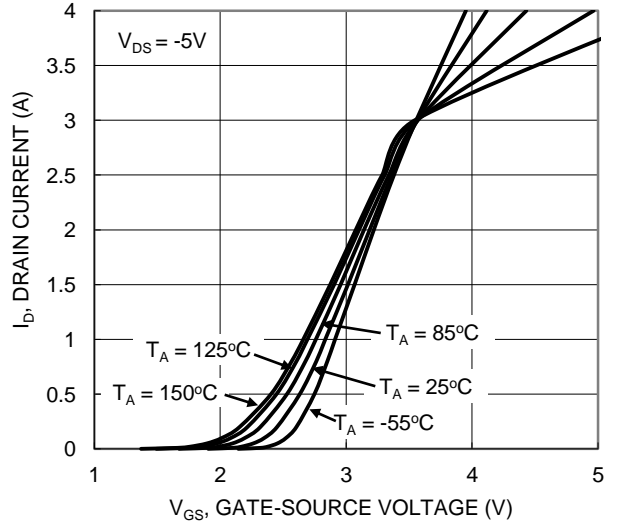


Figure 2. Typical Transfer Characteristic

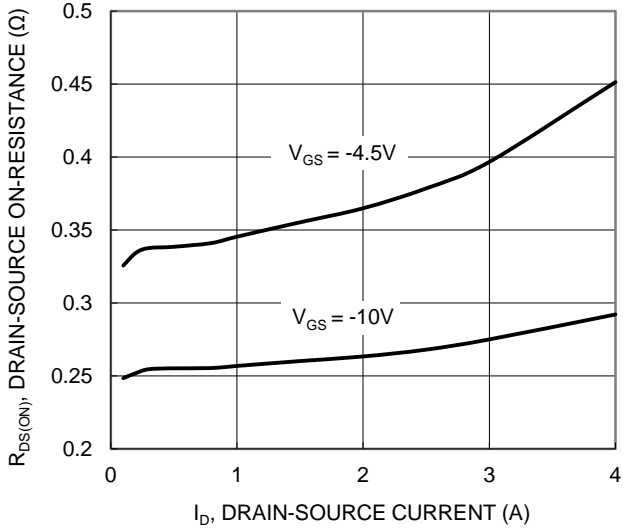


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

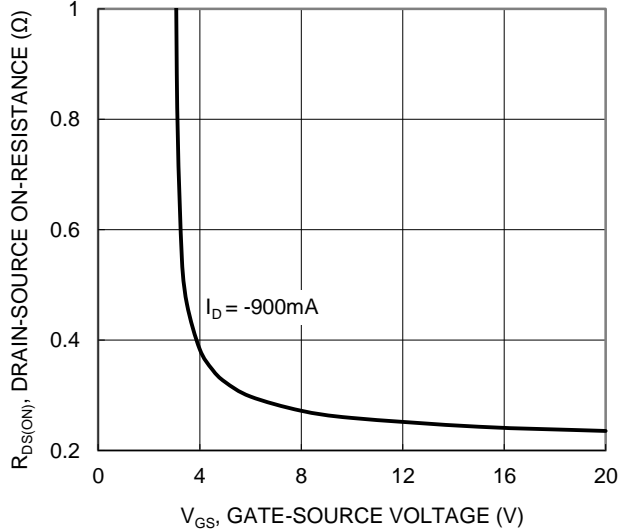


Figure 4. Typical Transfer Characteristic

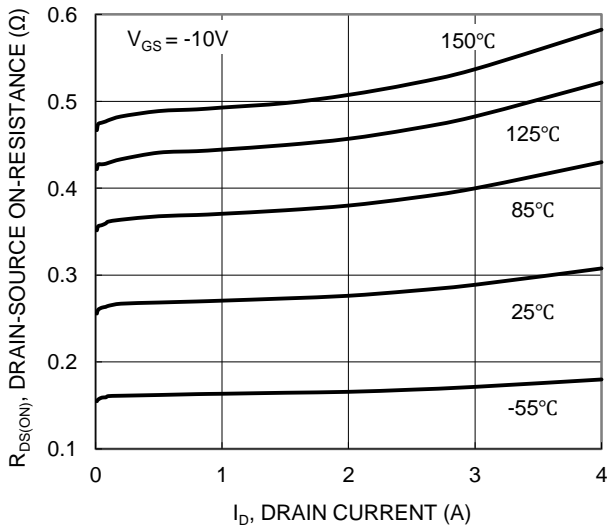


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

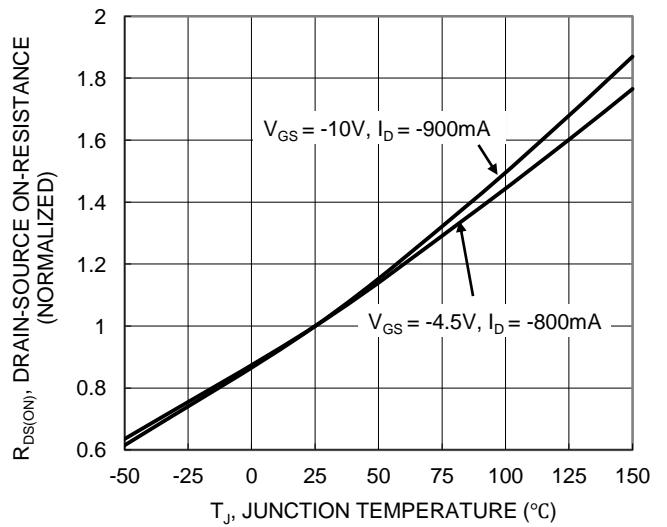


Figure 6. On-Resistance Variation with Junction Temperature

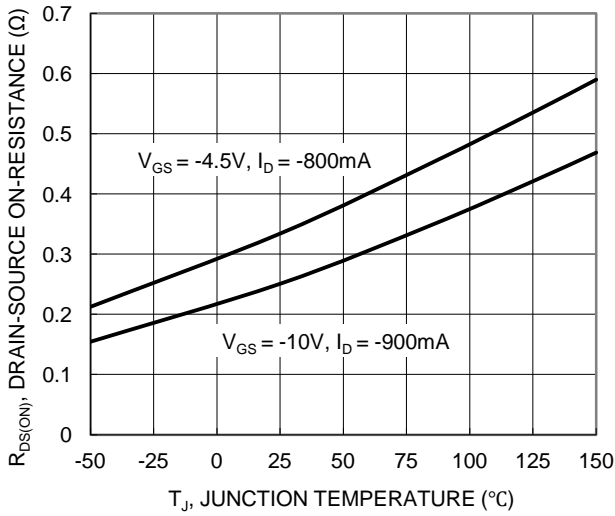


Figure 7. On-Resistance Variation with Junction Temperature

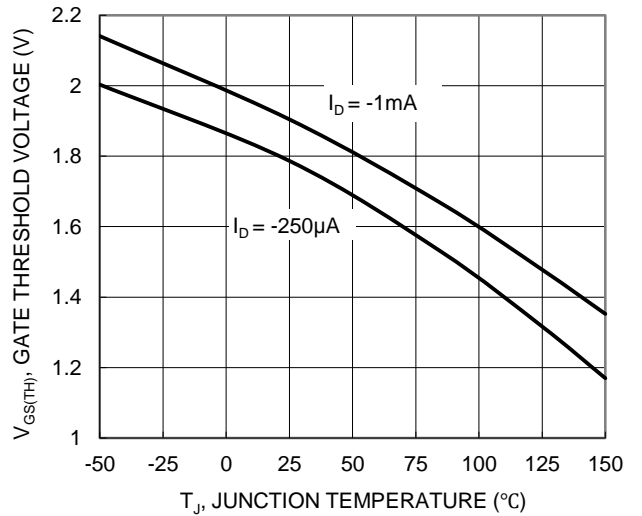


Figure 8. Gate Threshold Variation vs. Junction Temperature

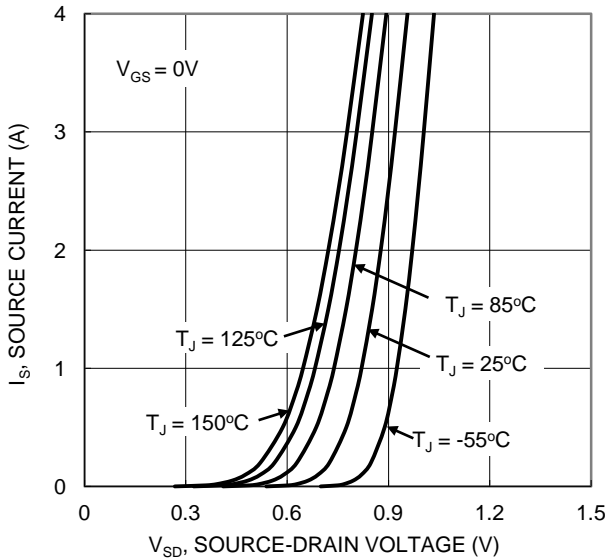


Figure 9. Diode Forward Voltage vs. Current

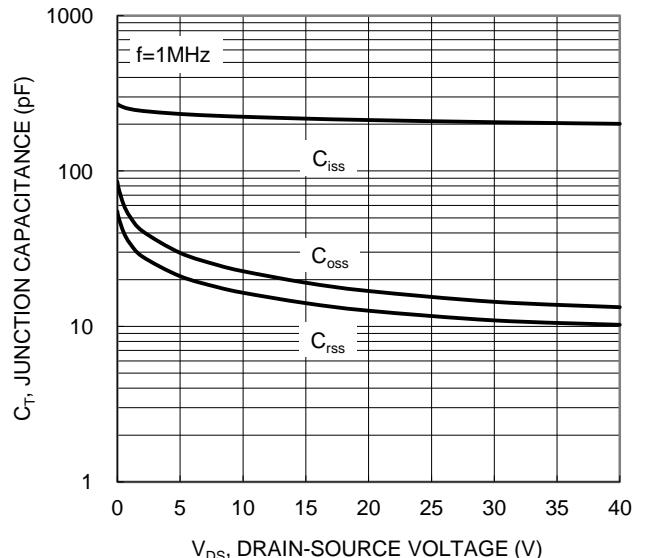


Figure 10. Typical Junction Capacitance

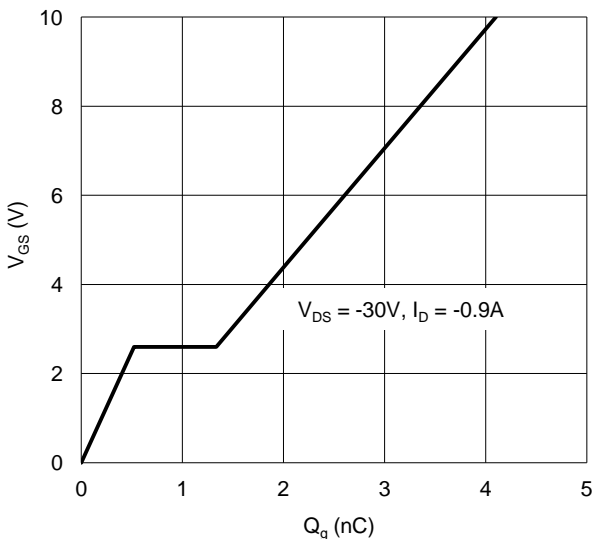


Figure 11. Gate Charge

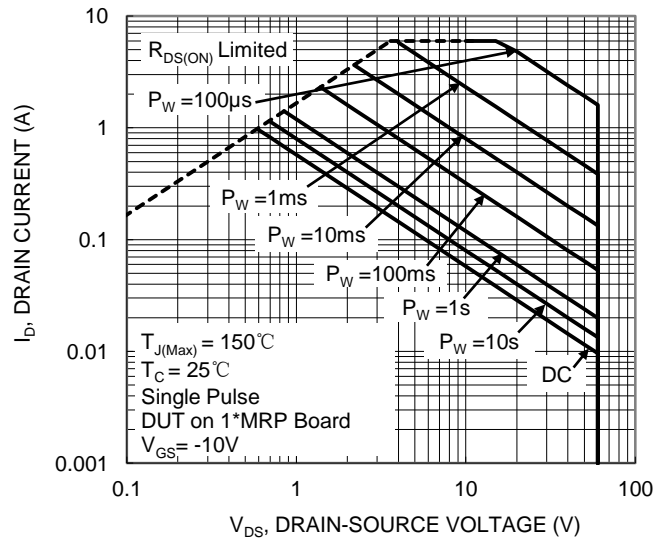


Figure 12. SOA, Safe Operation Area

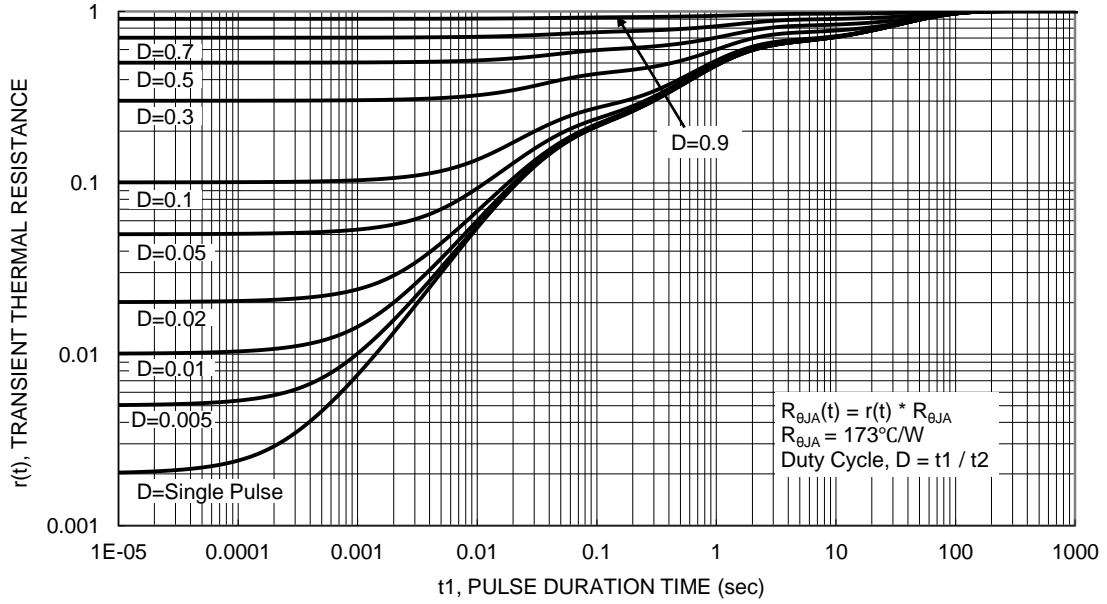
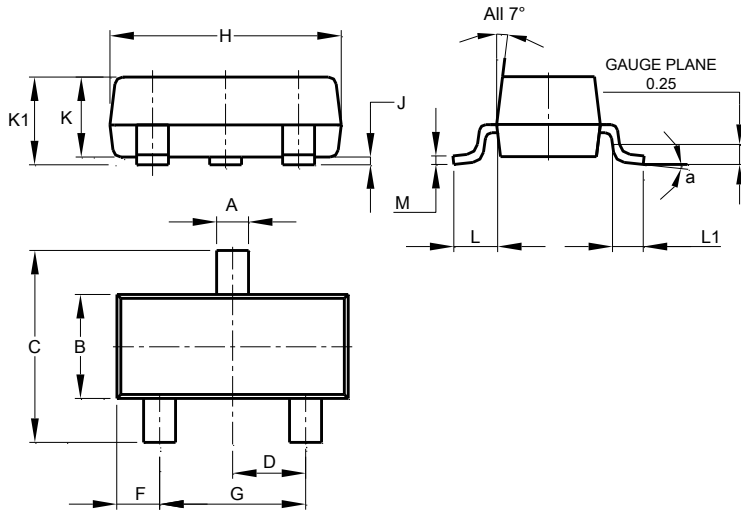


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

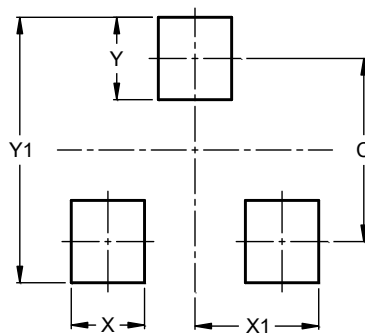


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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